

Contents

Abstract	ii
Abstrak	iii
Acknowledgement	iv
List of Publications	v
Contents	vi
List of Figures	x
List of Tables	xv
List of Abbreviations	xvii
1 Introduction	1
1.1 Development of Semiconductor Laser	1
1.2 Basics of Optical-fiber Telecommunication System	3
1.3 1.55 μm is the most efficient operation wavelength	4
1.4 Overview of the research	5
1.5 Dissertation Outline	7
2 Semiconductor Laser Review	8
2.1 Semiconductor Lasers Operation	8
2.2 Semiconductor Laser Material	10
2.3 Semiconductor Laser Design and Structure	12
2.3.1 Edge-emitting Lasers (EELs)	13
2.3.2 Surface-emitting Lasers (SELs)	14
2.3.3 Differences between EELs and VCSELs	14
2.4 Semiconductor Laser Characterization	15
2.4.1 Light-Current-Voltage (L-I-V) characteristics	15
2.4.2 Operating Mode characteristics	16
2.4.3 Spatial-mode characteristics	16
2.5 Reliability and Lifetime of Semiconductor Laser	17
2.6 Semiconductor Laser Applications	17

3	Fundamentals of VCSELs	20
3.1	VCSELs Development	20
3.2	Advantages of VCSELs over EELs	21
3.2.1	Fiber coupling efficiency	21
3.2.2	Emission capability	21
3.2.3	Operating mode	21
3.2.4	Low threshold current operation	22
3.2.5	Manufacturing efficiency	22
3.2.6	Component integration	22
3.2.7	Stable operation	22
3.3	VCSELs Basic Operation	23
3.4	VCSELs Material and Fabrication	23
3.5	VCSELs Structure	24
3.5.1	Distributed Bragg Reflector (DBR)	25
3.5.1 (a)	Epitaxially-grown mirror	26
3.5.1 (b)	Dielectric-deposited mirror	27
3.5.1 (c)	Wafer-fused mirror	28
3.5.2	Active region	29
3.5.2 (a)	InP-based active region	30
3.5.2 (b)	GaAs-based active region	31
3.5.3	Spacer	31
3.6	VCSELs Device Design	31
3.7	VCSELs Applications	33
4	Modeling and Computational Methods	34
4.1	Optics Calculation	34
4.1.1	Transfer Matrix Method	34
4.1.2	Phonon Rate Equation	37
4.2	Bulk Bandstructure Calculation	38
4.2.1	Distribution Functions	38
4.2.2	Direct Interband Transitions	40
4.2.3	Incorporating Many-Body Effects	41
4.2.4	Indirect Intraband Transitions	43
4.3	Quantum Well (QW) Calculation	44
4.4	Strain Effect Calculation	48

4.5	Carrier Transport Calculation	49
4.5.1	Poisson Equation and Charges	49
4.5.2	Carrier Distribution and Wavefunctions	50
4.5.3	Carrier Continuity Equations	51
4.5.4	Quantum Well Carrier Capture	52
4.5.5	Auger Recombination	53
4.5.6	Shockley-Read-Hall (SRH) Recombination	53
4.5.7	Interface Trap Recombination	54
4.5.8	Spontaneous Recombination	54
4.5.9	Stimulated Recombination	54
4.5.10	Carrier Current and Mobility	55
4.5.11	Temperature Dependent Mobility	55
4.5.12	Doping and Temperature Dependent Mobility Model	56
4.5.13	High Field Mobility	56
4.5.14	Material Interfaces	57
4.5.15	Lattice Heat Flow Equation	57
4.5.16	Thermal Conductivity	58
4.5.17	Energy Flux	58
4.5.18	Heat Sources	58
4.5.19	Thermal Boundary Conditions	59
4.6	Model for Spectral Broadening	59
4.7	Model for Material Parameters	60
5	Results and Discussion	61
5.1	DBR Mirror Component	61
5.1.1	InGaAsP/InP DBR Mirror Simulation	62
5.1.2	GaAs/AlGaAs DBR Mirror Simulation	66
5.1.3	SiC/MgO DBR Mirror Simulation	71
5.1.4	DBR mirror Discussion & 1.55 μm VCSELs DBR Mirror Proposed	73
5.2	Active Region Component	79
5.2.1	Strain Effect Simulation	79
5.2.2	Composition Effect Simulation	80
5.2.3	Quantum Well Thickness Effect Simulation	82
5.2.4	Number of Quantum Well Effect Simulation	83

5.2.5	Active Region Discussion & 1.55 μm VCSELs Active Region Proposed	84
5.3	Proposed Device Design for 1.55 μm VCSELs Diode	90
5.4	1.55 μm VCSELs Diode Device Characterization	91
5.4.1	1.55 μm VCSELs Diode Device Profile	92
5.4.2	1.55 μm VCSELs Diode Mode Analysis	94
5.4.3	1.55 μm VCSELs Diode PL Spectra	99
5.4.4	1.55 μm VCSELs Diode Emission Spectrum	100
5.4.5	1.55 μm VCSELs Diode L-I-V Characteristic	101
6	Conclusions and Future Work	105
Appendix A	Honeywell VCSELs Datasheet	107
Appendix B	Worldwide semiconductor laser sales	108
Bibliography		109

List of Figures

Chapter One

Figure 1.1	Applications of Optoelectronics and Photonics	1
Figure 1.2	Worldwide commercial laser revenues 1998 to 2002	3
Figure 1.3	Schematic diagram of optical-fiber telecommunication system	3
Figure 1.4	Fiber loss versus wavelength	4
Figure 1.5	Schematic design of VCSELs device	6

Chapter Two

Figure 2.1	Schematic diagram showing essential components of laser diode	8
Figure 2.2	Heavily doped p-n junction (a) in equilibrium (b) with forward bias	9
Figure 2.3	Band diagrams of (a) GaAs and (b) AlAs	10
Figure 2.4	Various combinations of compound semiconductors	11
Figure 2.5	Categorization of diode lasers structures. The two classifications at the bottom are not part of the family tree	12
Figure 2.6	Example of edge-emitting lasers	13
Figure 2.7	The divergence of a laser beam in the vertical and horizontal directions	14
Figure 2.8	Example of surface-emitting lasers	14
Figure 2.9	Wafer level differences between VCSELs and EELs	15
Figure 2.10	Typical L-I-V characteristic of a laser diode	16
Figure 2.11	Emission spectrum for laser devices such as LED EELs and VCSELs	16
Figure 2.12	Examples of (a) near-field and (b) far-field distributions of laser diode	17
Figure 2.13	L-I curve of laser diode as a function of temperature	17
Figure 2.14	Wavelength region and application	18

Chapter Three

Figure 3.1	Fiber coupling comparisons between VCSELs and EELs	21
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Figure 3.2	Basic operation differences between (a) EELs and (b) VCSELs The dashed arrow inside the schematic devices shows the path of light beam propagation.	23
Figure 3.3	Schematic structure of VCSELs device	25
Figure 3.4	Comparison of reflectivity in 1.55 μm VCSELs DBR mirror	26
Figure 3.5	Schematic of wafer-fusion process	28
Figure 3.6	The refractive index profile and the longitudinal electric field in the optical cavity within VCSELs	29
Figure 3.7	Schematics of some common VCSELs current confinement schemes (a) mesa-etch (b) Proton implantation (c) Oxide aperture and (d) Buried heterostructure	32
Figure 3.8	Double-fused VCSELs structure with oxidation aperture of AlGaAs	32
 Chapter Four		
Figure 4.1	Schematic energy band diagram of a (a) QW and (b) MQW	44
Figure 4.2	A schematic unstrained and strained-layer	48
Figure 4.3	Schematic illustration of the transport model	51
 Chapter Five		
Figure 5.1	Reflectivity for various n-DBR InGaAsP/InP composition	63
Figure 5.2	R_{max} and $R_{1.55}$ for various n-DBR InGaAsP/InP composition	63
Figure 5.3	Wavelength of R_{max} and Stopband for various n-DBR InGaAsP/InP composition	63
Figure 5.4	Reflectivity for various n-DBR InGaAsP/InP period	64
Figure 5.5	R_{max} and $R_{1.55}$ for various n-DBR InGaAsP/InP period	64
Figure 5.6	Reflectivity for various p-DBR InGaAsP/InP composition	65
Figure 5.7	R_{max} and $R_{1.55}$ for various p-DBR InGaAsP/InP composition	65
Figure 5.8	Wavelength of R_{max} and Stopband for various p-DBR InGaAsP/InP composition	65

Figure 5.9	Reflectivity for various p-DBR InGaAsP/InP period	66
Figure 5.10	R_{max} and $R_{1.55}$ for various p-DBR InGaAsP/InP period	66
Figure 5.11	Reflectivity for various n-DBR GaAs/AlGaAs composition	67
Figure 5.12	R_{max} and $R_{1.55}$ for various n-DBR GaAs/AlGaAs composition	67
Figure 5.13	Wavelength of R_{max} and Stopband for various n-DBR GaAs/AlGaAs composition	68
Figure 5.14	Reflectivity for various n-DBR GaAs/AlGaAs period	68
Figure 5.15	R_{max} for various n-DBR GaAs/AlGaAs period	69
Figure 5.16	Reflectivity for various p-DBR GaAs/AlGaAs composition	69
Figure 5.17	R_{max} and $R_{1.55}$ for various p-DBR GaAs/AlGaAs composition	70
Figure 5.18	Wavelength of R_{max} and Stopband for various p-DBR GaAs/AlGaAs composition	70
Figure 5.19	Reflectivity for various p-DBR GaAs/AlGaAs period	70
Figure 5.20	R_{max} for various p-DBR GaAs/AlGaAs period	71
Figure 5.21	(a) Reflectivity for various SiC/MgO period with (b) Stopband magnified	72
Figure 5.22	R_{max} for various siC/MgO period	72
Figure 5.23	Schematic illustration of the principle of DBR mirror with alternate high and low refractive index layers and its reflectance	73
Figure 5.24	Reflectivity spectrum for different p-DBR mirror material system	75
Figure 5.25	R_{max} versus number of periods for different p-DBR mirror material system	75
Figure 5.26	Absorption coefficient simulation for various n- & p-DBR material systems in the range of 1.4 μm to 1.75 μm .	78
Figure 5.27	Optical gain as function of emission wavelength for different strain (%)	80
Figure 5.28	Optical gain as function of strain (%) at 1.55 μm	80
Figure 5.29	Optical gain as function of emission wavelength for different composition (y)	81
Figure 5.30	Optical gain as function of composition (y) at 1.55 μm	81

Figure 5.31	G_{max} and wavelength of G_{max} as function of composition (y)	81
Figure 5.32	Optical gain as function of emission wavelength for different QW thickness (nm)	82
Figure 5.33	Optical gain as function of QW thickness (nm) at 1.55 μm	82
Figure 5.34	Optical gain as function of emission wavelength for different QW number	83
Figure 5.35	Optical gain as function of QW number at 1.55 μm	83
Figure 5.36	G_{max} and wavelength of G_{max} as function of QW number	84
Figure 5.37	Schematic band structure for (a) unstrained layer (b) compressive strained layer and (c) tensile strained layer	84
Figure 5.38	Optical gain as function of emission wavelength for different carrier density ($\times 10^{18}\text{cm}^{-3}$) at $T=300\text{K}$	87
Figure 5.39	Optical gain as function of carrier density at 1.55 μm and $T=300\text{K}$	87
Figure 5.40	Optical gain as function of emission wavelength for different temperature ($^{\circ}\text{C}$) at $N=5 \times 10^{18}\text{cm}^{-3}$	88
Figure 5.41	Optical gain as function of temperature ($^{\circ}\text{C}$) at 1.55 μm and $N=5 \times 10^{18}\text{cm}^{-3}$	89
Figure 5.42	(a) Schematic structure of the proposed 1.55 μm VCSELs diode with (b) middle structure is magnified	90
Figure 5.43	Non-uniform mesh generated for the 1.55 μm VCSELs structure	91
Figure 5.44	(a) Refractive index profile for the device structure and (b) with magnification	93
Figure 5.45	Net doping profile for the 1.55 μm VCSELs structure in horizontal cut	94
Figure 5.46	(a) Electron distribution and (b) Hole distribution inside the 1.55 μm VCSELs	94
Figure 5.47	Energy band diagram with (a) no applied bias and (b) forward bias	95
Figure 5.48	(a) Electron Fermi level and (b) Hole Fermi level with no applied bias	95
Figure 5.49	(a) Electron Fermi level and (b) Hole Fermi level with forward bias	95
Figure 5.50	The heavily doped band diagram (a) at equilibrium	96

and (b) with forward bias

Figure 5.51	Fundamental mode profile as a contour plot for the 1.55 μm VCSELs	97
Figure 5.52	Horizontal cut of the fundamental mode profile for the 1.55 μm VCSELs	97
Figure 5.53	3D plot of the fundamental mode profile for the 1.55 μm VCSELs	97
Figure 5.54	(a) Near-field contour plot and (b) in 3D plot for the 1.55 μm VCSELs	98
Figure 5.55	(a) Far-field vs. angle contour plot and (b) in 3D plot for the 1.55 μm VCSELs	99
Figure 5.56	Photoluminescence (PL) spectra of the 1.55 μm VCSELs	100
Figure 5.57	Optical spectrum of the 1.55 μm VCSELs	100
Figure 5.58	Light-current-voltage (L-I-V) characteristic of the 1.55 μm VCSELs	101
Figure 5.59	Voltage across of the active region and DBR shown in the L-I-V characteristic	102

List of Tables

Chapter One

Table 1.1	The development of Semiconductor Laser	2
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Chapter Two

Table 2.1	Binary systems showing the respective bandgap, (eV) and lattice constant, (Å)	11
Table 2.2	Materials for Light Sources	12

Chapter Three

Table 3.1	History of VCSELs research	20
Table 3.2	VCSELs material for various wavelength ranges	24
Table 3.3	Epitaxial mirror tuned to 1.55 μm . Each mirror contains high-index and low-index material, thermal conductivity (W/cmK) and refractive index values. The row-column crossing corresponds to the fractional refractive index ($\Delta n / \bar{n}$) percentage	26
Table 3.4	Amorphous mirrors tuned to 1.55 μm . Each mirror contains high-index and low-index material, thermal conductivity and refractive index values. The row-column crossing corresponds to the fractional refractive index ($\Delta n / \bar{n}$) percentage	27

Chapter Four

Table 4.1	Propagation constant in the direction of growth and electromagnetic field	35
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Chapter Five

Table 5.1	Internal parameters of n-DBR InGaAsP/InP mirror	62
Table 5.2	Internal parameters of p-DBR InGaAsP/InP mirror	64
Table 5.3	Internal parameters of n-DBR GaAs/AlGaAs mirror	66
Table 5.4	Internal parameters of p-DBR GaAs/AlGaAs mirror	69
Table 5.5	Internal parameters of SiC/MgO DBR mirror	71
Table 5.6	Optimum internal parameters and results for each DBR simulation	74
Table 5.7	Internal parameters for InGaAsP active region simulation	79

Table 5.8	Internal parameters for proposed InGaAsP active region simulation	86
Table 5.9	Schematic structure with the internal parameters for 1.55 μm VCSELs diode	91
Table 5.10	The proposed 1.55 μm VCSELs diode simulation results in comparison with the highest performance 1.55 μm Double-fused VCSELs	103

List of Abbreviations

1D	One-Dimensional
2D	Two-Dimensional
3D	Three-Dimensional
Al₂O₃	Alumina Oxide
AlAs	Aluminum Arsenide
AlAsSb	Aluminum Arsenide Antimony
AlGaAs	Aluminum Gallium Arsenide
AlGaAsSb	Aluminum Gallium Arsenide Antimony
AlGaInAs	Aluminum Gallium Indium Arsenide
AlGaN	Aluminum Gallium Nitride
AlInAs	Aluminum Indium Arsenide
AlInGaAs	Aluminum Indium Gallium Arsenide
a-Si	Amorphous Silica
CD	Compact Disc
CO₂	Carbon Dioxide
CW	Continuous Wave
DBR	Distributed Bragg Reflector
DFB	Distributed Feedback
DH	Double Heterojunction
DSM	Dynamic Single Mode
EDFA	Erbium Doped Fiber Amplifiers
EELs	Edge-Emitting Lasers
FTTH	Fiber-to-the-House
GaAs	Gallium Arsenide
GaAsSb	Gallium Arsenide Antimony
GaInAsSb	Gallium Indium Arsenide Antimony
GaInNAs	Gallium Indium Nitride Arsenide
GaInNAs	Gallium Indium Nitride Arsenide
GaN	Gallium Nitride
GSMBE	Gas-source Molecular Beam Epitaxy
InAlGaP	Indium Aluminum Gallium Phosphide
InGaAs	Indium Gallium Arsenide
InGaAsP	Indium Gallium Arsenide Phosphide
InGaN	Indium Gallium Nitride
InP	Indium Phosphide
IR	Infra-Red
KP	Kronnig-Penney
LED	Light Emitting Diode
L-I	Light-Current
L-I-V	Light-Current-Voltage
LO	Longitudinal Optical
MBE	Molecular Beam Epitaxy
MgO	Magnesium Oxide
MOCVD	Metal-organic Chemical Vapor Deposition
MQW	Multi Quantum Well
PbSeTe	Lead Selenium Tellurium
PbSnSeTe	Lead Tin Selenium Tellurium
PCM	Pulse-Code-Modulated
PECVD	Plasma-enhanced Chemical-Vapor Deposition
PL	Photoluminescence

QW	Quantum Well
SELs	Surface-Emitting Lasers
SiC	Silica Carbide
SiO₂	Silica Dioxide
SRH	Shockley-Read-Hall
TE	Transverse Electric
TM	Transverse Magnetic
TMM	Transfer Matrix Method
VCD	Video Compact Disc
VCSELs	Vertical-Cavity Surface-Emitting Lasers
V-I	Voltage-Current
WDM	Wavelength-Division Multiplexing
ZnCdSe	Zinc Cadmium Selenium
ZnSe	Zinc Selenium